

ABSTRACT

ESD protection circuit and method for fabricating the same, which has an improved performance, the method including the steps of (1) forming a transistor on a substrate, (2) forming a first insulating film on the substrate inclusive of the transistor and having a first contact hole to an input terminal of the transistor, (3) forming a buffered layer in the first contact hole and the first insulating film in the vicinity of the first contact hole, (4) forming a second insulating film on the first insulating film inclusive of the buffered layer and having a second contact hole to the buffered layer, and (5) forming a pad both on the second contact hole and the second insulating film in the vicinity of the second contact hole.